TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

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AUDIO FREQUENCY LOW POWER AMPLIFIER APPLICATIONS

DRIVER STAGE AMPLIFIER APPLICATIONS

SWITCHING APPLICATIONS

• Excellent hFE Linearity

: $h_{FE(2)} = 25$ (Min.) at $V_{CE} = -6V$, $I_{C} = -400$ mA

• High Voltage : $V_{CEO} = -50V$ (Min.)

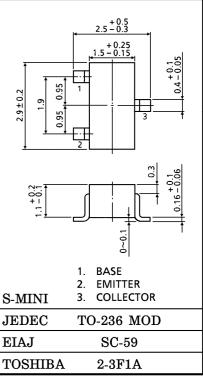
• Complementary to 2SC3325

Small Package

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	-50	V
Collector-Emitter Voltage	v_{CEO}	-50	V
Emitter-Base Voltage	v_{EBO}	-5	V
Collector Current	$I_{\mathbf{C}}$	-500	mA
Base Current	$I_{\mathbf{B}}$	-50	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	200	mW
Junction Temperature	$T_{ m j}$	150	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C

Unit in mm



Weight: 0.012g

Marking

Type Name

hFE Rank

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -50V, I_{E} = 0$	_	_	-0.1	μ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB} = -5V, I_C = 0$	_	-	-0.1	μ A
DC Current Gain	hFE (1) (Note)	$V_{CE} = -1V, I_{C} = -100 \text{mA}$	70	_	240	
	h _{FE (2)} (Note)	$V_{CE} = -6V, I_{C} = -400 \text{mA}$	25	_	_	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$	_	-0.1	-0.25	V
Base-Emitter Voltage	$ m V_{BE}$	$V_{CE} = -1V, I_{C} = -100 \text{mA}$	-	-0.8	-1.0	V
Transition Frequency	${ m f_T}$	$V_{CE} = -6V, I_{C} = -20mA$	_	200	_	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -6V, I_E = 0, f = 1MHz$	_	13	_	pF

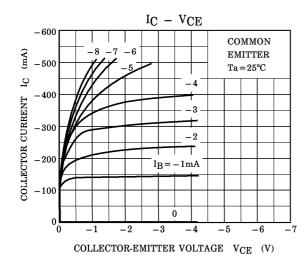
Note: hFE(1) Classification

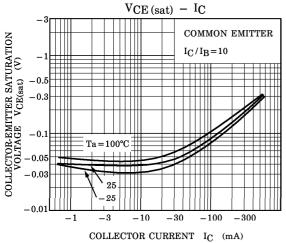
 $O:70\sim140, Y:120\sim240$

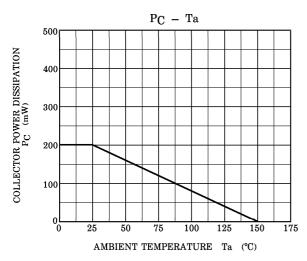
hFE (2) Classification

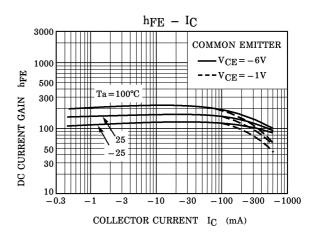
O: 25 (Min.) Y: 40 (Min.)

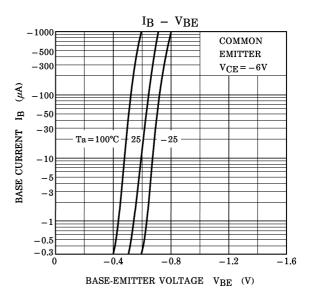
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